L Number	Hits	Search Text	DB	Time stamp
-	48003	thin adj film adj transistor	USPAT;	2004/06/22 12:46
1 1			US-PGPUB;	
]			EPO; JPO;	
1			DERWENT;	
1 !		·	IBM_TDB	
-	198	thin adj film adj transistor adj array adj panel	USPAT;	2004/06/22 12:47
-			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	155	(thin adj film adj transistor adj array adj panel) and (pixel adj	USPAT;	2004/06/22 12:48
		electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	92	(thin adj film adj transistor adj array adj panel) and ((pixel adj	USPAT;	2004/06/22 12:49
		electrode) with passiv\$6)	US-PGPUB;	
j l			EPO; JPO;	
]			DERWENT;	
]	_		IBM_TDB	
-	87	((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 12:51
		adj electrode) with passiv\$6)) and ((drain adj electrode) same	US-PGPUB;	
		(contact adj hole))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	88	((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 12:51
		adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB;	
		(contact adj hole)	EPO; JPO;	
			DERWENT;	
		transfer of the state of the state of the second second second the second secon	IBM_TDB	0004/00/00 40:50
-	88	(((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 12:52
		adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB;	!
		(contact adj hole)) and passiv\$6	EPO; JPO; DERWENT;	
			IBM_TDB	
	78	((((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 13:55
_	, 0	adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB;	2004/00/22 10:50
		(contact adj hole)) and passiv\$6) and (ohmic adj contact)	EPO; JPO;	
	-	(contact adj noic)) and passive of and (offine adj contact)	DERWENT:	
			IBM_TDB	
_	3	(((((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 12:59
	}	adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB:	
		(contact adj hole)) and passiv\$6) and (ohmic adj contact))	EPO; JPO;	
1		and ((polysilicon with insulating) same doped)	DERWENT;	
		<b>5</b> ,,	IBM_TDB	
-	0	(((((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 13:57
		adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB;	
		(contact adj hole)) and passiv\$6) and (ohmic adj contact))	EPO; JPO;	
		and (photoresist\$4 same pattern\$4 same impurity)	DERWENT;	
'			IBM_TDB	
-	57	(((((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 15:02
		adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB;	
i		(contact adj hole)) and passiv\$6) and (ohmic adj contact))	EPO; JPO;	
	[	and (photoresist\$4 same pattern\$4)	DERWENT;	
		<u> </u>	IBM_TDB	
-	57	((((((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 15:02
[		adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB;	
[		(contact adj hole)) and passiv\$6) and (ohmic adj contact))	EPO; JPO;	
		and (photoresist\$4 same pattern\$4)) and impurity	DERWENT;	
L			IBM_TDB	

	· · · · · ·		LICOAT	0004/00/00 46 55
-	1	((((((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 13:58
		adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB;	
		(contact adj hole)) and passiv\$6) and (ohmic adj contact))	EPO; JPO;	
		and ((polysilicon with insulating) same doped)) and	DERWENT;	
	1	(photoresist\$4 same pattern\$4)	IBM_TDB	
-	0	(((((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 15:06
		adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB;	
		(contact adj hol )) and passiv\$6) and (ohmic adj contact))	EPO; JPO;	
	<b>!</b>	and ((photoresist\$4 with pattern\$4) same (polysilicon near3	DERWENT;	
		mask))	IBM TDB	
_	57	(((((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 15:06
		adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB:	
		(contact adj hole)) and passiv\$6) and (ohmic adj contact))	EPO; JPO;	
		and (photoresist\$4 with pattern\$4)	DERWENT;	
	į		IBM_TDB	
_	0	((((((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 15:07
		adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB;	
		(contact adj hole)) and passiv\$6) and (ohmic adj contact))	EPO; JPO;	
		and (photoresist\$4 with pattern\$4)) and (polysilicon near3	DERWENT;	,
		mask)	IBM_TDB	
_	l 0	((((((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT:	2004/06/22 15:07
		adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB:	
		(contact adj hole)) and passiv\$6) and (ohmic adj contact))	EPO; JPO;	
		and (photoresist\$4 with pattern\$4)) and (polysilicon with	DERWENT:	
		mask)	IBM TDB	
_	57	((((((thin adj film adj transistor adj array adj panel) and ((pixel	USPAT;	2004/06/22 15:08
		adj electrode) with passiv\$6)) and (drain adj electrode) and	US-PGPUB;	200 1700722 10.00
		(contact adj hole)) and passiv\$6) and (ohmic adj contact))	EPO; JPO;	
		and (photoresist\$4 with pattern\$4)) and mask	DERWENT;	
·		and (photorosisty + that patterny + )) and mask	IBM TDB	
	i	<u> </u>	םטוי_וטט	